

PF01411A

MOS FET Power Amplifier Module for E-GSM Handy Phone

HITACHI

ADE-208-433C (Z)
4th Edition
February 1997

Application

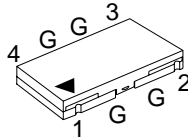
- For E-GSM class4 880 to 915 MHz
- For 4.8V nominal battery use

Features

- High gain 3stage amplifier : 0 dBm input
- Lead less thin & Small package : 2 mm Max, 0.2cc
- High efficiency : 45% Typ at 3.8 W
- Wide gain control range : 90 dB Typ

Pin Arrangement

• RF-K



1: Pin
2: V_{apc}
3: V_{dd}
4: P_{out}
G: GND

Absolute Maximum Ratings (T_c = 25°C)

Item	Symbol	Rating	Unit
Supply voltage	V _{DD}	10	V
Supply current	I _{DD}	3	A
V _{APC} voltage	V _{APC}	4	V
Input power	P _{in}	10	mW
Operating case temperature	T _c (op)	-30 to +100	°C
Storage temperature	T _{stg}	-30 to +100	°C
Output power	P _{out}	5	W

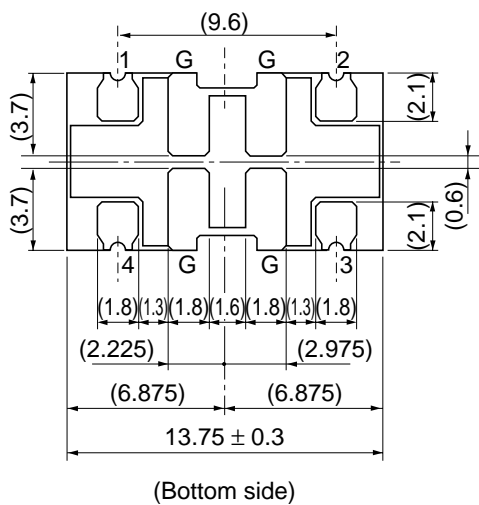
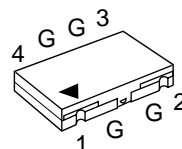
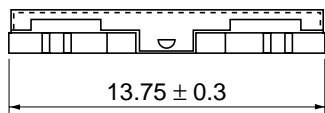
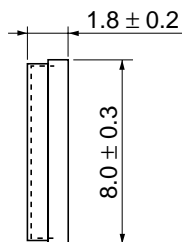
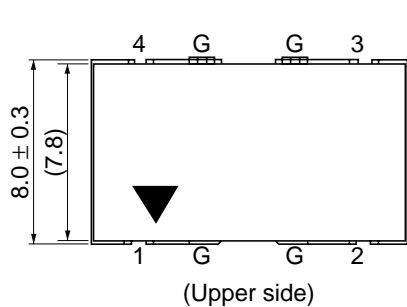
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Electrical Characteristics (T_c = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Frequency range	f	880	—	915	MHz	
Control voltage range	V _{APC}	0.5	—	3.0	V	
Drain cutoff current	I _{DS}	—	—	100	μA	V _{DD} = 10 V, V _{APC} = 0 V
Total efficiency	η _T	40	45	—	%	Pin = 1 mW, V _{DD} = 4.8 V,
2nd harmonic distortion	2nd H.D.	—	-45	-35	dBc	Pout = 3.8 W, V _{apc} = controlled
3rd harmonic distortion	3rd H.D.	—	-45	-35	dBc	R _L = R _g = 50 Ω, T _c = 25°C
Input VSWR	VSWR (in)	—	1.5	3	—	
Output power (1)	Pout (1)	3.8	4.3	—	W	Pin = 1 mW, V _{DD} = 4.8 V, V _{APC} = 3.0 V, R _L = R _g = 50 Ω, T _c = 25°C
Output power (2)	Pout (2)	2.5	2.9	—	W	Pin = 1 mW, V _{DD} = 4.3 V, V _{APC} = 3.0 V, R _L = R _g = 50 Ω, T _c = 80°C
Isolation	—	—	-50	-40	dBm	Pin = 1 mW, V _{DD} = 4.8 V, V _{APC} = 0.5 V, R _L = R _g = 50 Ω, T _c = 25°C
Switching time	tr, tf	—	1	2	μs	Pin = 1 mW, V _{DD} = 4.8 V, Pout = 3.8 W, R _L = R _g = 50 Ω, T _c = 25°C
Stability & Load VSWR tolerance	—	No parasitic oscillation & No degradation			—	Pin = 1 mW, V _{DD} = 4 to 7 V, Pout ≤ 3.8 W, V _{apc} ≤ 3 V GSM pulse. R _g = 50 Ω, t = 20sec., T _c = 25°C, Output VSWR = 6 : 1 All phases

Package Dimensions

Unit: mm



Remark:
Coplanarity of bottom side of terminals
are less than 0 ± 0.1 mm.

Hitachi Code	RF-K
JEDEC	—
EIAJ	—
Weight (reference value)	—

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